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Sommario/riassunto

The discovery of the quantized and fractional Quantum Hall Effect phenomena is among the most important physics findings in the latter half of this century. The precise quantization of the electrical resistance involved in the quantized Hall effect phenomena has led to the new definition of the resistance standard and has metrologically affected all of science and technology. This resource consists of contributions from the top researchers in the field who present recent experimental and theoretical developments. Each chapter is self-contained and includes its own set of references guiding rea